
**Listing of Claims**

1. (Original) A method of manufacturing a microelectronics device, comprising:

providing a substrate having an active layer, a dielectric layer and a structural layer, wherein the active layer is formed over the dielectric layer and the dielectric layer is formed over the structural layer;

forming an opening through the active layer thereby exposing a surface of the dielectric layer and defining active layer sidewalls; and

forming a spacer covering a first portion of the exposed dielectric layer surface and substantially spanning one of the active layer sidewalls.

2. (Original) The method of claim 1 further comprising forming an etch stop layer over the active layer, wherein the opening is formed through the active layer and the etch stop layer thereby defining etch stop layer sidewalls substantially aligned with the active layer sidewalls, wherein the spacer substantially spans one of the active layer sidewalls and one of the etch stop layer sidewalls.

3. (Original) The method of claim 1 further comprising:

cleaning at least a second portion of the exposed dielectric layer surface.

4. (Original) The method of claim 3 wherein the cleaning includes chemical etching with an etchant chemistry comprising hydrofluoric acid.

5. (Original) The method of claim 3 wherein the cleaning includes plasma etching.

6. (Original) The method of claim 5 wherein the plasma etching includes a plasma chemistry comprising fluorine.

7. (Original) The method of claim 3 wherein the cleaning includes vapor etching.

8. (Original) The method of claim 1 further comprising forming a gate electrode over the active layer.

9. (Original) The method of claim 1 further comprising forming a silicide layer over the active layer.

10. (Original) The method of claim 1 wherein the spacer comprises silicon dioxide.

11. (Original) The method of claim 1 wherein the active layer comprises strained silicon.

12. (Original) The method of claim 1 wherein the active layer has a thickness ranging between about 100 Angstroms and about 1000 Angstroms.

13-24. Cancelled.